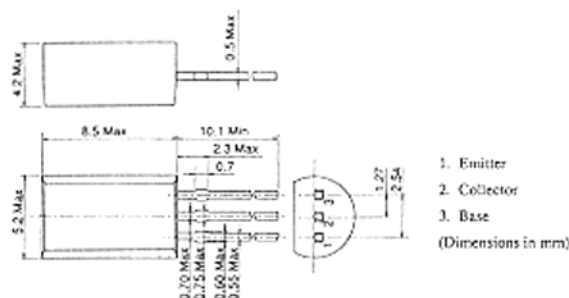


2SD666, 2SD666A

SILICON NPN EPITAXIAL

LOW FREQUENCY HIGH VOLTAGE AMPLIFIER

Complementary pair with 2SB646/A



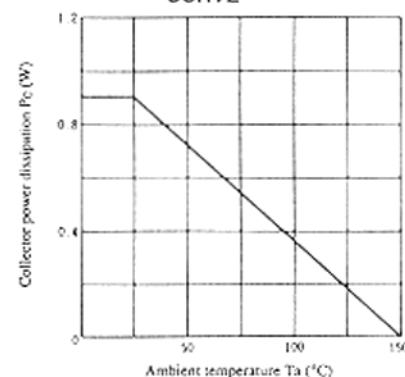
1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

(JEDEC TO-92 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SD666	2SD666A	Unit
Collector to base voltage	V _{CB0}	120	120	V
Collector to emitter voltage	V _{CEO}	80	100	V
Emitter to base voltage	V _{EBO}	5	5	V
Collector current	I _C	50	50	mA
Collector peak current	i _{C(peak)}	100	100	mA
Collector power dissipation	P _C	0.9	0.9	mW
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

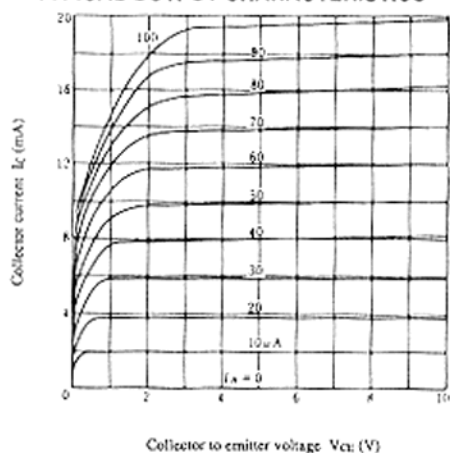
Item	Symbol	Test Condition	2SD666			2SD666A			Unit
			min.	typ.	max.	min.	typ.	max.	
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	120	—	—	120	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	80	—	—	100	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5	—	—	5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = 100V, I _E = 0	—	—	10	—	—	10	μA
DC current transfer ratio	h _{FE1} *	V _{CE} = 5V, I _C = 10mA	60	—	320	60	—	200	
	h _{FE2}	V _{CE} = 5V, I _C = 1mA	30	—	—	30	—	—	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 30mA, I _B = 3mA	—	—	2	—	—	2	V
Base to emitter voltage	V _{BE}	V _{CE} = 5V, I _C = 10mA	—	—	1.5	—	—	1.5	V
Gain bandwidth product	f _T	V _{CE} = 5V, I _C = 10mA	—	140	—	—	140	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	3	—	—	3	—	pF

* The 2SD666 and 2SD666A are grouped by h_{FE1} as follows.

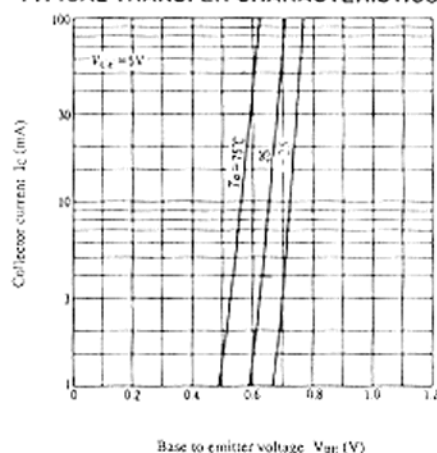
	B	C	D
2SD666	60 to 120	100 to 200	160 to 320
2SD666A	60 to 120	100 to 200	—

2SD666, 2SD666A

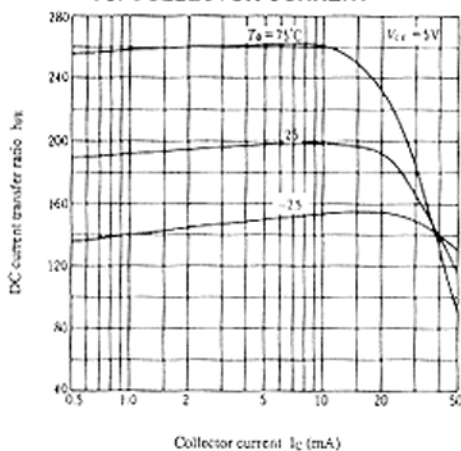
TYPICAL OUTPUT CHARACTERISTICS



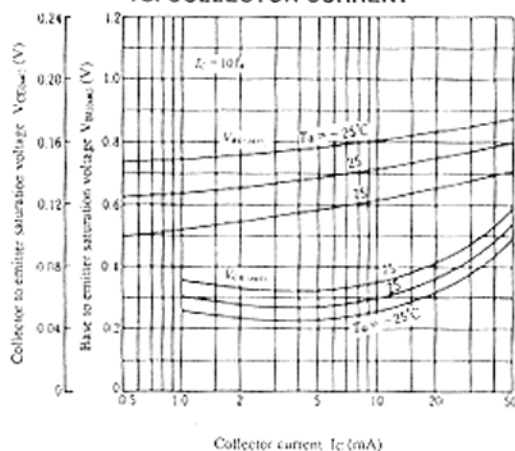
TYPICAL TRANSFER CHARACTERISTICS



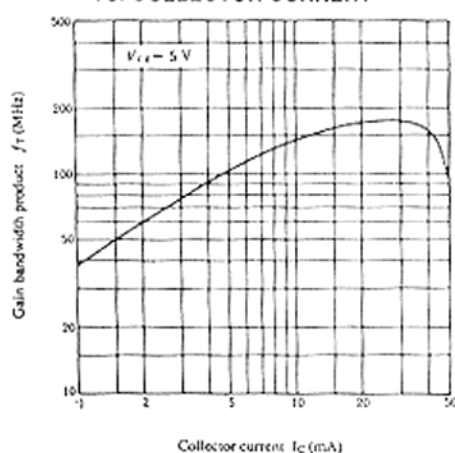
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



SATURATION VOLTAGE VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE

